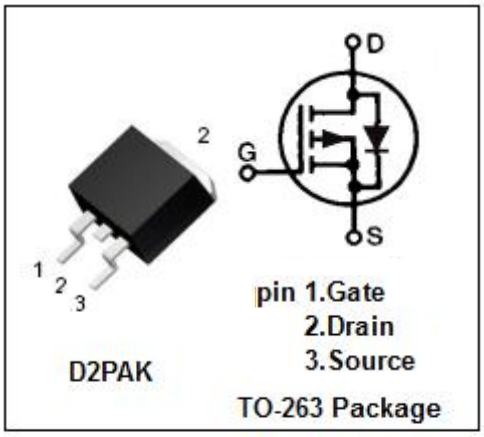
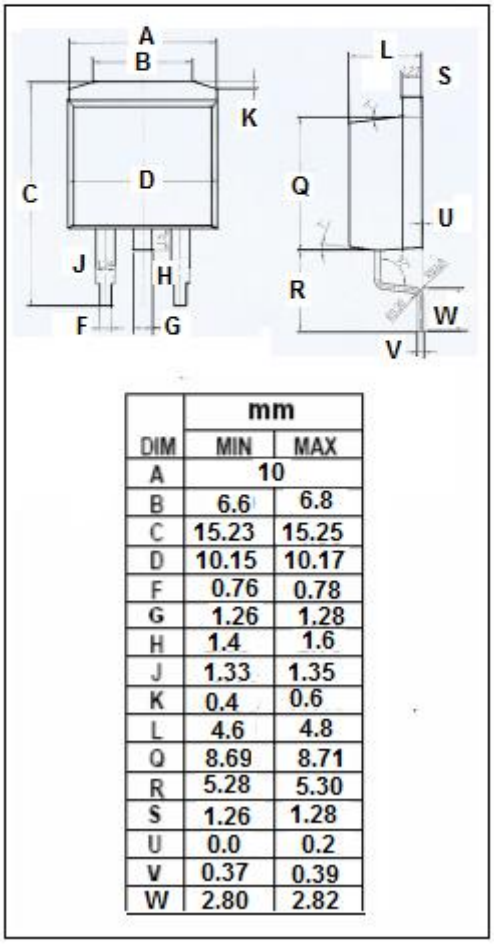
isc P-Channel MOSFET Transistor IXTA28P065T



- **FEATURES**
- Static drain-source on-resistance:
  $R_{DS}(on) \leqslant 45m\Omega$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

- **APPLICATION**
- Hight side switching
- Current regulators
- Automatic test equipment



DIM	mm MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	-65	V
V_{GS}	Gate-Source Voltage	±15	V
I_D	Drain Current-Continuous	-28	A
I_{DM}	Drain Current-Single Pulsed	-90	A
P_D	Total Dissipation @T_C=25℃	83	W
T_j	Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Channel-to-case thermal resistance	1.5	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= -250 μA	-65			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D= -250 μA	-2.5		-4.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= -10V; I_D= -14A			45	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±15V; V_{DS}=0			±50	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= V_{DSS}; V_{GS}= 0V			-3	μA
		V_{DS}= V_{DSS}; V_{GS}= 0V; T_J=125℃			-100	
V_{SD}	Diode forward voltage	I_F= -28A; V_{GS} = 0V			-1.5	V